

MOS MEMORIES

■ 16MDRAM (5V version, CBR self refresh operation)

Supply voltage: 4.5 ~ 5.5V

Organization (words × bits)	Type No.	Access time max. (ns)	Cycle time min. (ns)	Refresh (cycles/ms)	Maximum Supply Current		Package	No.	Remarks
					Active (mA)	Standby (μ A)			
16M × 1	MN4216100ASJ	60/70	110/130	4096/128	80/70	250	SOJ026-P-0300B	M11	Fast page mode
	MN4216100ATT	60/70	110/130	4096/128	80/70	250	TSOP026-P-0300B	M21	Fast page mode
	MN4217100ASJ	60/70	110/130	2048/128	120/105	250	SOJ026-P-0300B	M11	Fast page mode
	MN4217100ATT	60/70	110/130	2048/128	120/105	250	TSOP026-P-0300B	M21	Fast page mode
4M × 4	MN4216400ASJ	60/70	110/130	4096/128	80/70	250	SOJ026-P-0300B	M11	Fast page mode
	MN4216400ATT	60/70	110/130	4096/128	80/70	250	TSOP026-P-0300B	M21	Fast page mode
	MN4217400ASJ	60/70	110/130	2048/128	120/105	250	SOJ026-P-0300B	M11	Fast page mode
	MN4217400ATT	60/70	110/130	2048/128	120/105	250	TSOP026-P-0300B	M21	Fast page mode
1M × 16	MN4216160ASJ	60/70	110/130	4096/128	90/80	350	SOJ042-P-0400	M14	Fast page mode 2CAS · 1WE
	MN4216160ATT	60/70	110/130	4096/128	90/80	350	TSOP050-P-0400A	M24	Fast page mode 2CAS · 1WE
	▲MN4216165ASJ	60/70	110/130	4096/128	90/80	350	SOJ042-P-0400	M14	EDO mode 2CAS · 1WE
	▲MN4216165ATT	60/70	110/130	4096/128	90/80	350	TSOP050-P-0400A	M24	EDO mode 2CAS · 1WE

▲Under development

■ 16MDRAM (3.3V version, CBR self refresh operation)

Supply voltage: 3.0 ~ 3.6V

Organization (words × bits)	Type No.	Access time max. (ns)	Cycle time min. (ns)	Refresh (cycles/ms)	Maximum Supply Current		Package	No.	Remarks
					Active (mA)	Standby (μ A)			
16M × 1	MN42V16100ASJ	60/70	110/130	4096/128	70/60	200	SOJ026-P-0300B	M11	Fast page mode
	MN42V16100ATT	60/70	110/130	4096/128	70/60	200	TSOP026-P-0300B	M21	Fast page mode
	MN42V17100ASJ	60/70	110/130	2048/128	110/95	200	SOJ026-P-0300B	M11	Fast page mode
	MN42V17100ATT	60/70	110/130	2048/128	110/95	200	TSOP026-P-0300B	M21	Fast page mode
4M × 4	MN42V16400ASJ	60/70	110/130	4096/128	70/60	200	SOJ026-P-0300B	M11	Fast page mode
	MN42V16400ATT	60/70	110/130	4096/128	70/60	200	TSOP026-P-0300B	M21	Fast page mode
	MN42V17400ASJ	60/70	110/130	2048/128	110/95	200	SOJ026-P-0300B	M11	Fast page mode
	MN42V17400ATT	60/70	110/130	2048/128	110/95	200	TSOP026-P-0300B	M21	Fast page mode
1M × 16	MN42V16160ATT	60/70	110/130	4096/128	90/80	250	TSOP050-P-0400A	M24	Fast page mode 2CAS · 1WE
	MN42V18160ATT	60/70	110/130	1024/128	180/160	250	TSOP050-P-0400A	M24	Fast page mode 2CAS · 1WE
	▲MN42V16165ATT	60/70	110/130	4096/128	90/80	250	TSOP050-P-0400A	M24	EDO mode 2CAS · 1WE
	▲MN42V18165ATT	60/70	110/130	1024/128	180/160	250	TSOP050-P-0400A	M24	EDO mode 2CAS · 1WE

▲Under development

■ 16M Synchronous DRAM (3.3V version, CBR self refresh operation)

Supply voltage: 3.0 ~ 3.6V

Organization (words × bits)	Type No.	Cycle time min. (ns)	Refresh (cycles/ms)	Maximum Supply Current		Package	No.	Remarks
				Active (mA)	Standby (μ A)			
512k × 16 × 2	▲MN4SV17160T	10/12/15	2048/32	120/110/100	1000	TSOP050-P-0400	M26	LVTTTL

▲Under development

(Package Symbol) SOJ = S small-Q outline J-Bend Package, TSOP = T hin S small Q outline P package